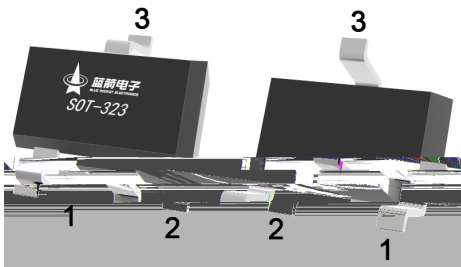
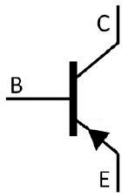


SOT-323 PNP Silicon PNP transistor in a SOT-323 Plastic Package.

Low current, Low voltage, HF Product.

General purpose amplifier and switching.



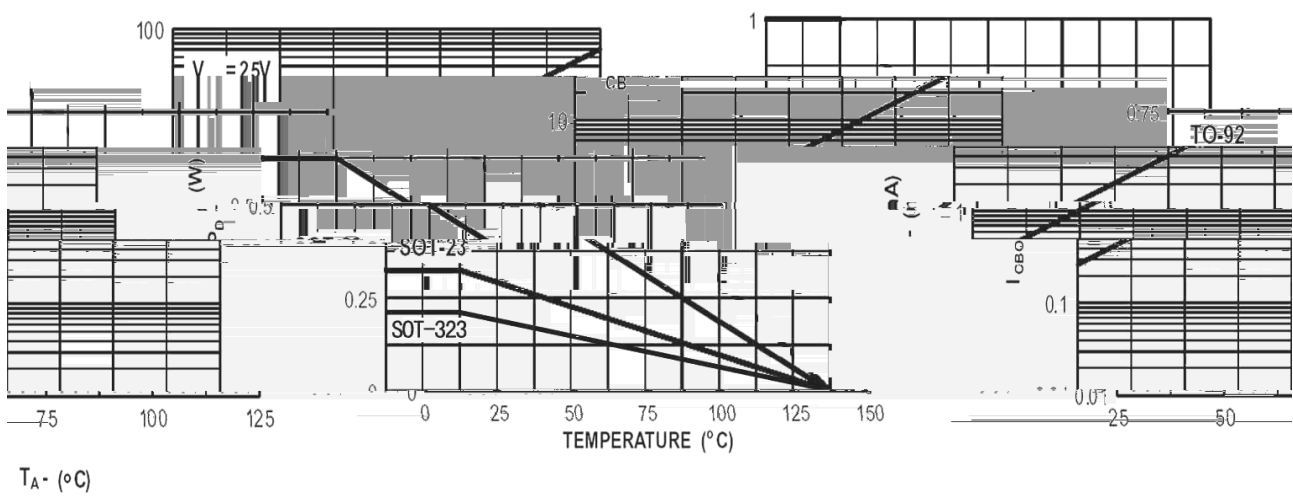
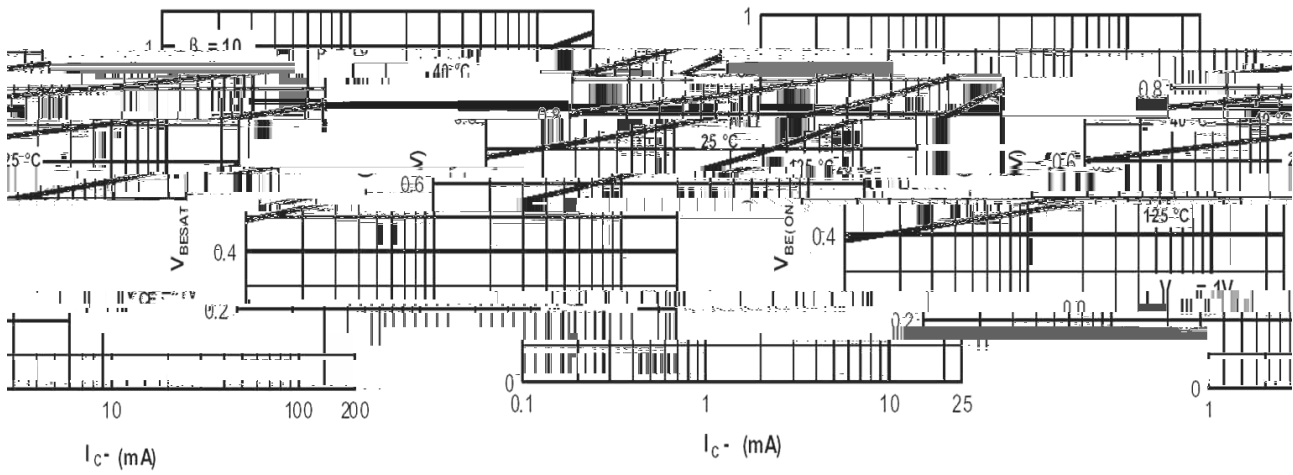
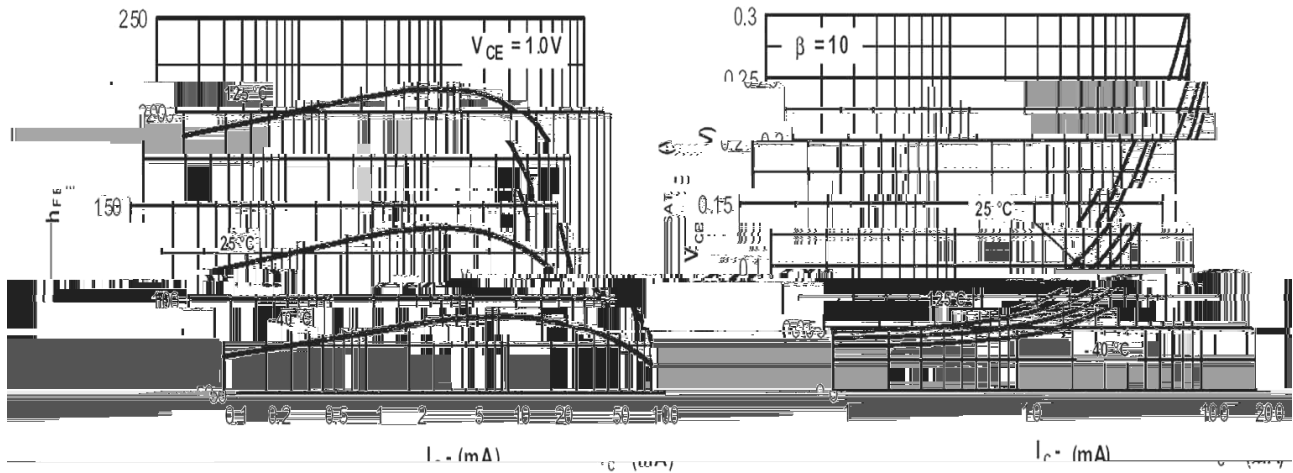
PIN1 Base PIN 2 Emitter PIN 3 Collector

Marking	H2A
---------	-----

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

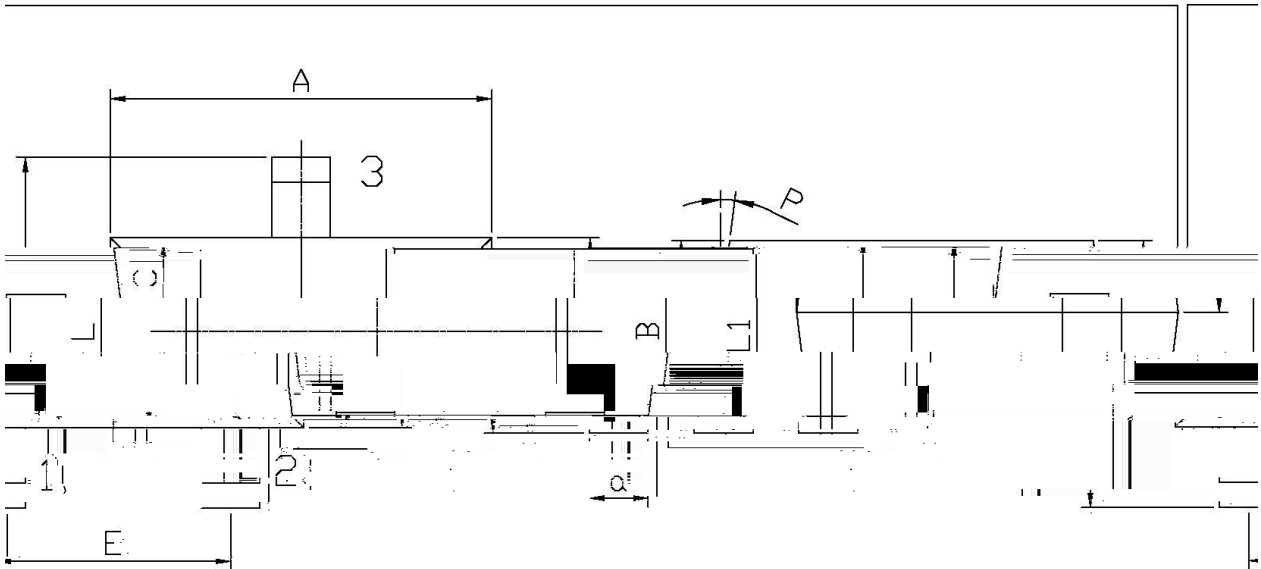
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -10\mu A$ $I_E = 0$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-40			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -10\mu A$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -30V$ $I_E = 0$			-0.05	μA
Emitter to Base Current	I_{EBO}	$V_{EB} = -3.0V$ $I_C = 0$			-0.05	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -1.0V$ $I_C = -10mA$	100		300	
	$h_{FE(2)}$	$V_{CE} = -1.0V$ $I_C = -100mA$	30			
	$h_{FE(3)}$	$V_{CE} = -1.0V$ $I_C = -50mA$	60			
	$h_{FE(4)}$	$V_{CE} = -1.0V$ $I_C = -1.0mA$	80			
	$h_{FE(5)}$	$V_{CE} = -1.0V$ $I_C = -0.1mA$	60			
Collector to Emitter Saturation Voltage	$V_{CE(sat) (1)}$	$I_C = -10mA$ $I_B = -1.0mA$			-0.25	V
	$V_{CE(sat) (2)}$	$I_C = -50mA$ $I_B = -5.0mA$			-0.4	V
Base to Emitter Saturation Voltage	$V_{BE(sat) (1)}$	$I_C = -10mA$ $I_B = -1.0mA$	-0.65		-0.85	V
	$V_{BE(sat) (2)}$	$I_C = -50mA$ $I_B = -5.0mA$			-0.95	V

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Transition Frequency	f_T	$I_C=-10mA$ $V_{CE}=-20V$ $f=100MHz$	250			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-5.0V$ $f=1.0MHz$			4.5	pF
Storage Time	t_{stg}	$V_{CC}=-3.0V$ $I_C=-10mA$ $I_{B1}=-I_{B2}=-1.0mA$			225	ns
Fall Time	t_f	$V_{CC}=-3.0V$ $I_C=-10mA$ $I_{B1}=-I_{B2}=-1.0mA$			75	ns
Delay Time	t_d	$V_{CC}=-3.0V$ $V_{BE}=-0.5V$ $I_C=-10mA$ $I_{B1}=-1.0mA$			35	ns
Rise Time	t_r	$V_{CC}=-3.0V$ $V_{BE}=-0.5V$ $I_C=-10mA$ $I_{B1}=-1.0mA$			35	ns
Input Capacitance	C_{ib}	$V_{EB}=-0.5V$ $f=1.0MHz$			10	pF

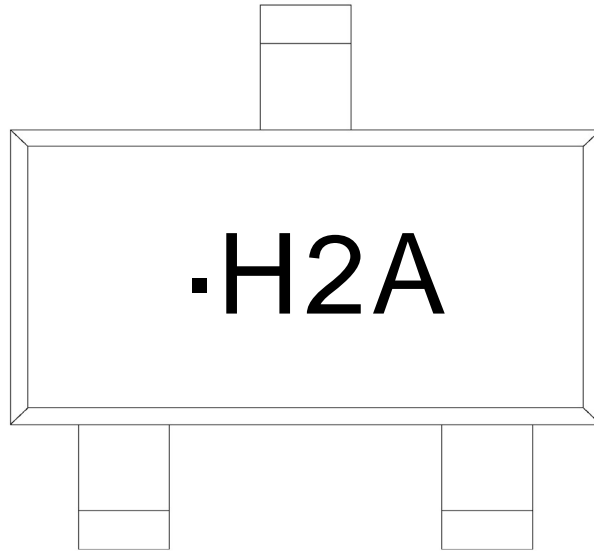


SPT-323

单位: mm



	Symbol		Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max	Min	Max		Min	Max
	1.95	2.35	C	0.30	0.50		A
E	2.00	2.2	L1	0.85	1.15		
E	1.20	1.40	alpha	0.20	0.40		
B	1.15	1.35	P		7°		



·

H

2A

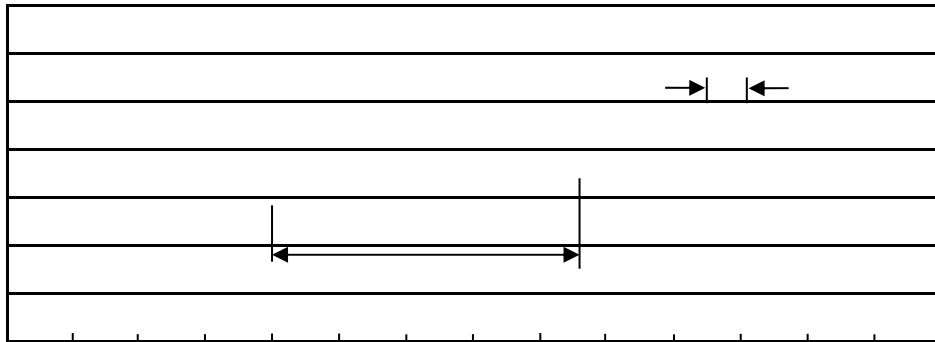
Note:

·

Identify

H: Company Code

2A: Product Type Code

Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- | | | | |
|---|---------|-----------|---|
| 1 | 150 180 | 60 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | 2 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
SOT-323	3,000	10	30,000	6	180,000	7 x8	180x120x180	390x385x205